

# US1A THRU US1M

## SMAG Plastic-Encapsulate Diodes

### High Efficient Rectifier

#### Features

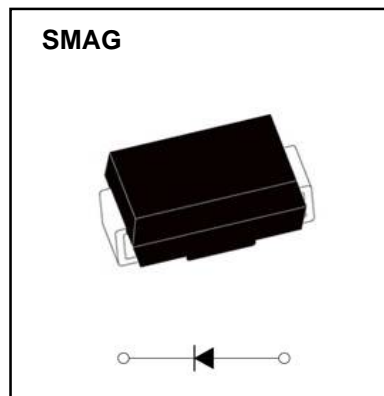
- $I_o$  1A
- $V_{RRM}$  50V-1000V
- High surge current capability
- Glass passivated chip
- Polarity: Color band denotes cathode

#### Applications

- Rectifier

#### Marking

- US1X
- X : From A To M



#### Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	US							
				1A	1B	1D	1F	1G	1J	1K	1M
Repetitive Peak Reverse Voltage	$V_{RRM}$	V		50	100	200	300	400	600	800	1000
Maximum RMS Voltage	$V_{RMS}$	V		35	70	140	210	280	420	560	700
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave, Resistance load, $T_L=115^\circ\text{C}$	1.0							
Surge(Non-repetitive)Forward Current	$I_{FSM}$	A	60Hz Half-sine wave, 1 cycle, $T_a=25^\circ\text{C}$	30							
Junction Temperature	$T_J$	$^\circ\text{C}$		-55 ~ +150							
Storage Temperature	$T_{STG}$	$^\circ\text{C}$		-55 ~ +150							

#### Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	US							
				1A	1B	1D	1F	1G	1J	1K	1M
Peak Forward Voltage	$V_{FM}$	V	$I_{FM}=1.0\text{A}$	1.0		1.3		1.7			
Peak Reverse Current	$I_{RRM1}$	$\mu\text{A}$	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$							
	$I_{RRM2}$			$T_a=125^\circ\text{C}$							
Reverse Recovery time	$t_r$	ns	$I_F=0.5\text{A}$ $I_R=1\text{A}$ $I_{RR}=0.25\text{A}$	50					75		
Thermal Resistance(Typical)	$R_{\theta J-A}$	$^\circ\text{C/W}$	Between junction and ambient	75 <sup>1)</sup>							
	$R_{\theta J-L}$		Between junction and terminal	27 <sup>1)</sup>							

#### Notes:

Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

# Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

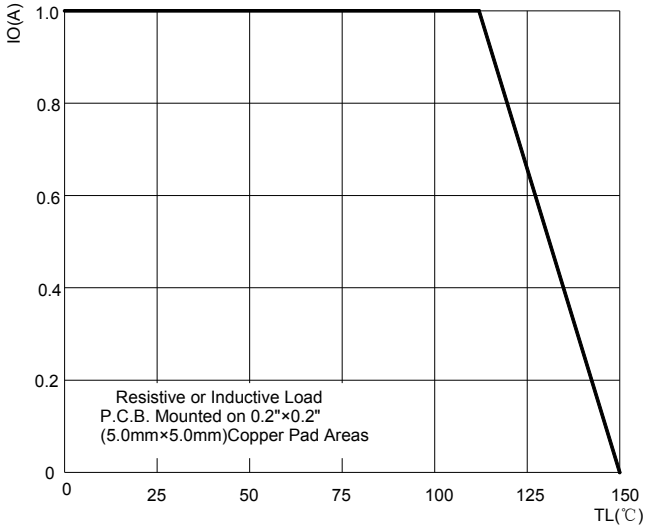


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

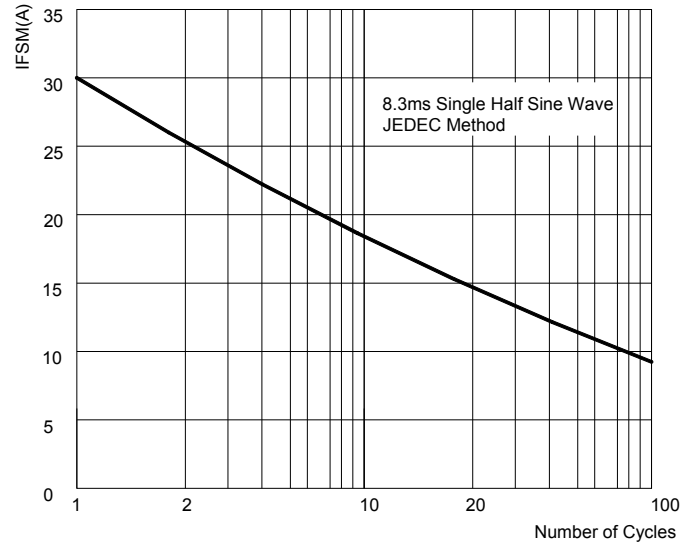


FIG.3: TYPICAL FORWARD CHARACTERISTICS

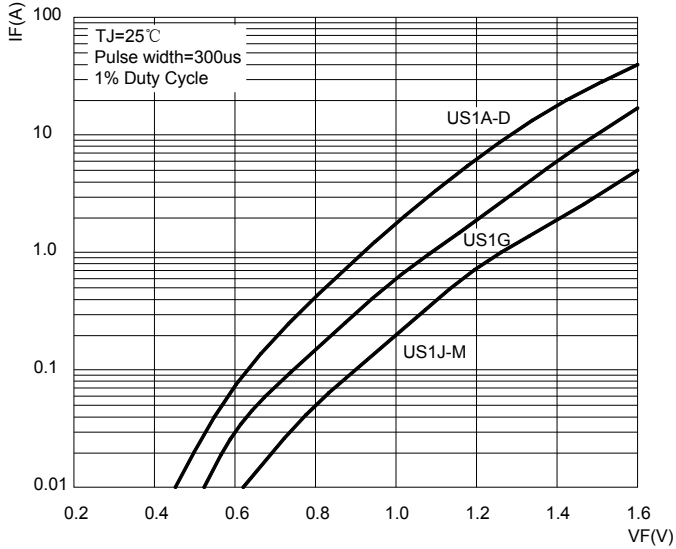


FIG.4: TYPICAL REVERSE CHARACTERISTICS

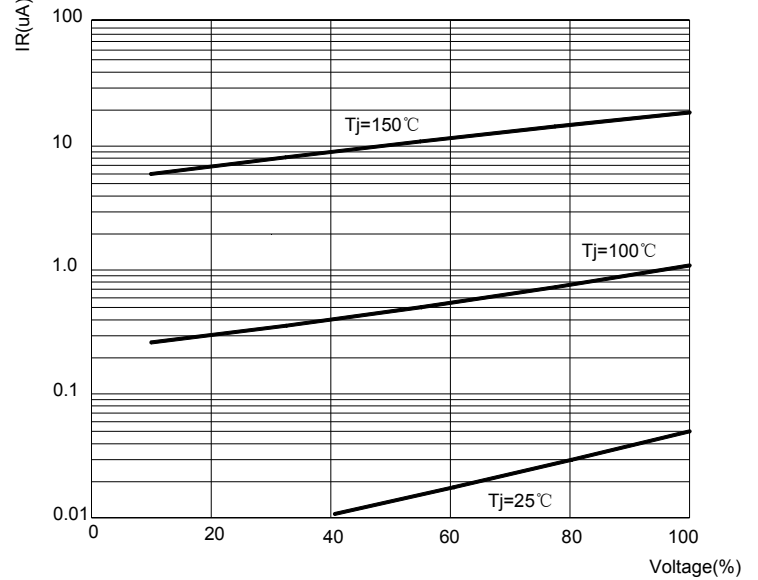
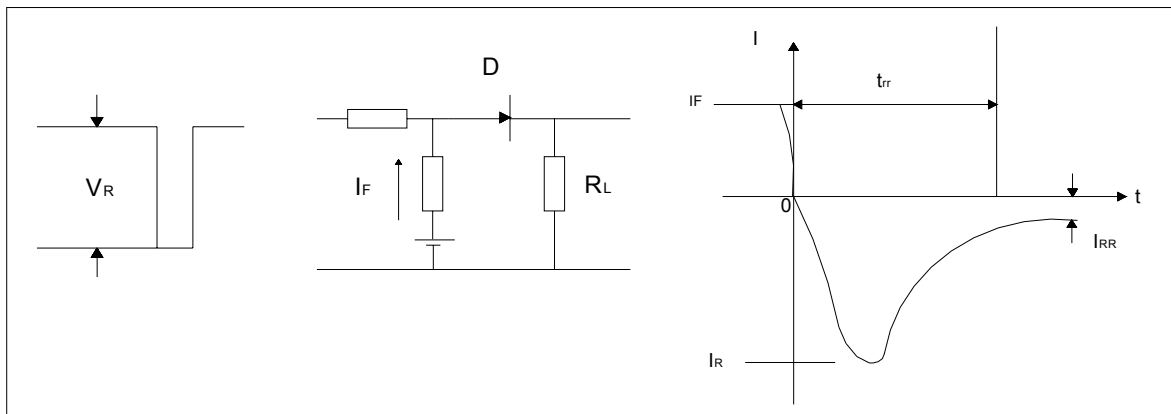
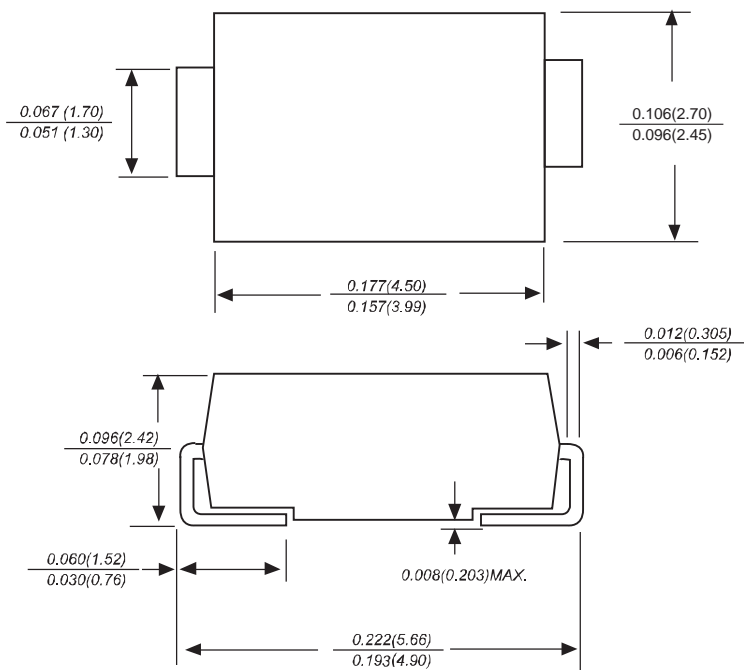


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

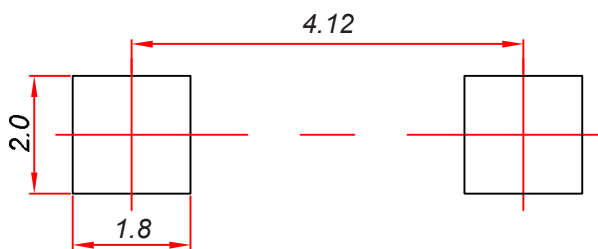


## SMAG Package Outline Dimensions



Dimensions in inches and (millimeters)

## SMAG Suggested Pad Layout



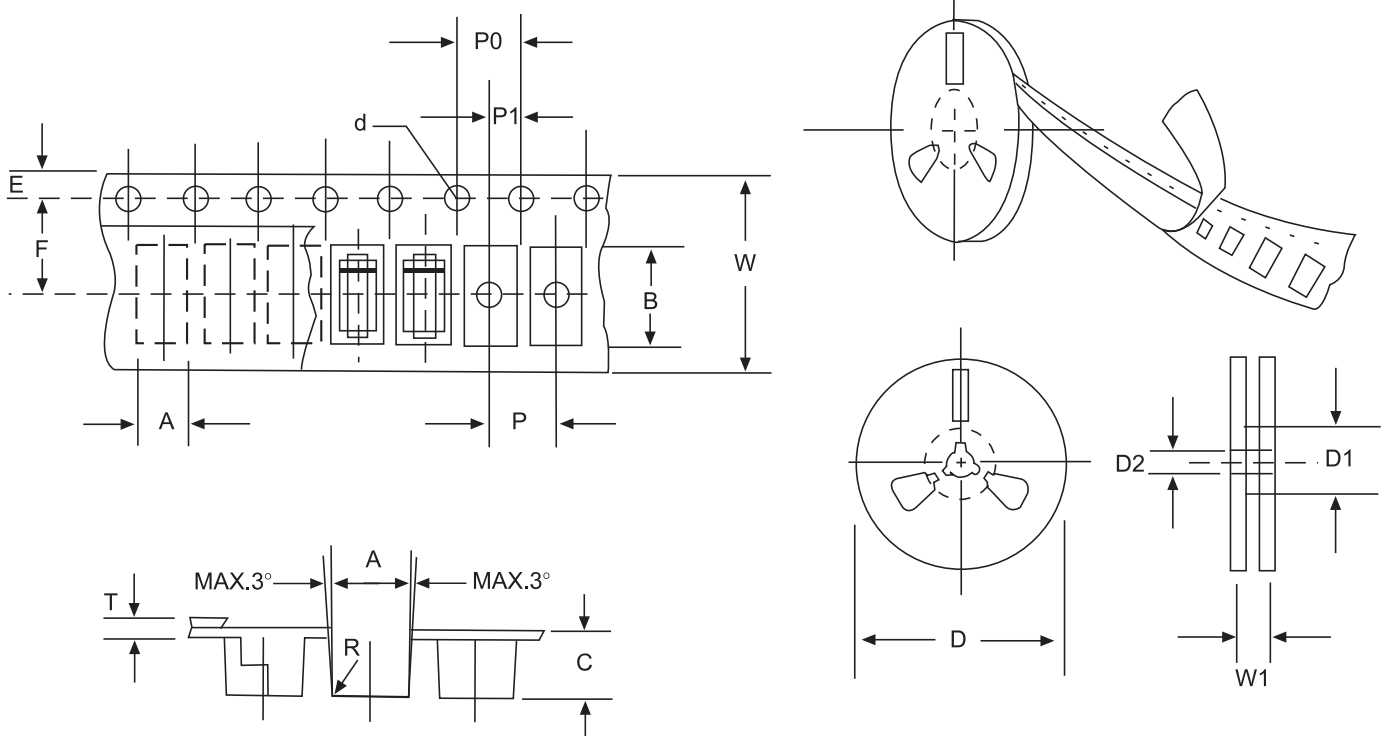
**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$ mm.
3. The pad layout is for reference purposes only.

**NOTICE**

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## Reel Taping Specifications For Surface Mount Devices- SMAG



**Fig:CONFIGURATION OF FLAT MELF TAPING**

ITEM	SYMBOL	SMAG mm(inch)
Carrier width	A	2.79±0.1(0.110±0.004)
Carrier length	B	5.33±0.1(0.210±0.004)
Carrier depth	C	2.36±0.1(0.093±0.004)
Sprocket hole	d	1.55±0.05(0.061±0.002)
Reel outside diameter	D	279±2.0 (11± 0.079)
Reel inner diameter	D1	75±1.0 ( 2.95 ±0.039)
Feed hole diameter	D2	13±0.5(0.512±0.020)
Sprocket hole position	E	1.75±0.1(0.069±0.004)
Punch hole position	F	5.5±0.05(0.217±0.002)
Punch hole pitch	P	4.0±0.1(0.157±0.004)
Sprocket hole pitch	P0	4.0±0.1(0.157±0.004)
Embossment center	P1	2.0±0.1(0.079±0.004)
Totall tape thickness	T	0.28±0.02(0.011 ±0.0008)
Tape width	W	12.0±0.2(0.472±0.008)
Reel width	W1	16.8±2.0(0.661±0.079)

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.